

● PRINTER RUSH ●
(PTO ASSISTANCE)

Application : 10/716366 Examiner : Smart GAU : 2813

From: CA

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<input type="checkbox"/> 1449	<hr/>	<input type="checkbox"/> Continuing Data
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<input type="checkbox"/> SPEC	<hr/>	

[RUSH] MESSAGE: Claim 10 lacks final period
Please Resub Thank You CD

[XRUSH] RESPONSE: JK

INITIALS DR

NOTE: This form will be included as part of the official USPTO record, with the Response document coded as XRUSH.
REV 10/04

10. (Currently Amended) A method for making a transistor device by laser synthesis directly onto a monolithic substrate ~~of~~ essentially of a crystalline or polycrystalline wide-bandgap semiconductor compound, said method comprising, the steps of:

- a. providing a monolithic wide-bandgap semiconductor compound substrate having a reverse side ~~and~~ of essentially n-type semiconductive carriers responsive to laser synthesis conversion;
- b. converting a first section of said substrate to a p-type semiconductive carrier by laser synthesis;
- c. converting a second section of said substrate to a p-type semiconductive carrier by laser synthesis spaced apart from said first p-type carrier section, to thereby form a separation therebetween;
- d. inscribing on said substrate by laser synthesis a first conductor connected to said first p-type section and a second conductor connected to said second p-type section, to provide electrical connections to said first and second p-type sections, respectively;
- e. inscribing on said reverse side of said substrate a third ~~said p-type section~~ sections on said substrate, and a third conductor, said third conductors providing means for connecting said device to other ~~and~~ external components, elements and circuits, and to thereby provide a p-n-p type semiconductor transistor.

11. (Original) A method for making a transistor device of claim 10, which includes the steps of placing said p-n-p transistor in a hermetically sealed chamber having a laser beam transmission window therein, and forming a first dielectric layer on a surface of said substrate disposed between said spaced apart p-type carrier sections and a second conductor layer on top of said dielectric layer by means of laser synthesis and various selected metallo-organic gases introduced into said chamber, and said laser